



**THE DATASHEET OF
MJE15033G**



MJE15032 (NPN), MJE15033 (PNP)

Complementary Silicon Plastic Power Transistors

Designed for use as high-frequency drivers in audio amplifiers.

Features

- High DC Current Gain
- High Current Gain – Bandwidth Product
- TO-220 Compact Package
- Epoxy Meets UL 94 V-0 @ 0.125 in
- These Devices are Pb-Free and are RoHS Compliant*

MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|--|----------------|--------------|--------------------------|
| Collector-Emitter Voltage | V_{CE0} | 250 | Vdc |
| Collector-Base Voltage | V_{CB} | 250 | Vdc |
| Emitter-Base Voltage | V_{EB} | 5.0 | Vdc |
| Collector Current – Continuous | I_C | 8.0 | Adc |
| Collector Current – Peak | I_{CM} | 16 | Adc |
| Base Current | I_B | 2.0 | Adc |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 50 0.40 | W W/ $^\circ\text{C}$ |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 2.0 0.016 | W W/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range | T_J, T_{stg} | -65 to +150 | $^\circ\text{C}$ |
| ESD – Human Body Model | HBM | 3B | V |
| ESD – Machine Model | MM | C | V |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|------|---------------------------|
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 2.5 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 62.5 | $^\circ\text{C}/\text{W}$ |

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

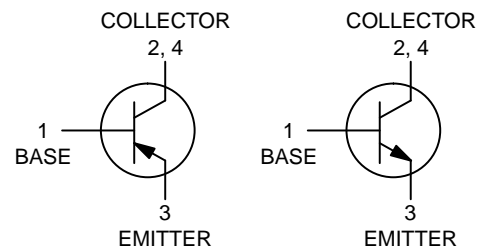


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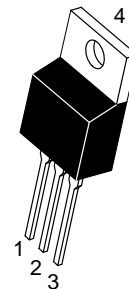
<http://onsemi.com>

8.0 AMPERES POWER TRANSISTORS COMPLEMENTARY SILICON 250 VOLTS, 50 WATTS

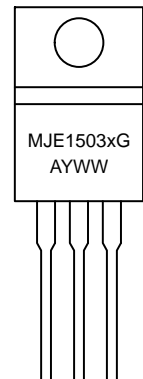
COMPLEMENTARY



MARKING DIAGRAM



**TO-220
CASE 221A
STYLE 1**



MJE1503x = Specific Device Code
 x = 2 or 3
 A = Assembly Location
 Y = Year
 WW = Work Week
 G = Pb-Free Package

ORDERING INFORMATION

| Device | Package | Shipping |
|-----------|---------------------|---------------|
| MJE15032G | TO-220 (Pb-Free) | 50 Units/Rail |
| MJE15033G | TO-220 (Pb-Free) | 50 Units/Rail |

MJE15032 (NPN), MJE15033 (PNP)

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|--|-----------------------|----------------|-------------|------------------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Sustaining Voltage (Note 1) (I _C = 10 mA _{dc} , I _B = 0) | V _{CEO(sus)} | 250 | – | V _{dc} |
| Collector Cutoff Current (V _{CB} = 250 V _{dc} , I _E = 0) | I _{CBO} | – | 10 | μA _{dc} |
| Emitter Cutoff Current (V _{BE} = 5.0 V _{dc} , I _C = 0) | I _{EBO} | – | 10 | μA _{dc} |
| ON CHARACTERISTICS (Note 1) | | | | |
| DC Current Gain (I _C = 0.5 A _{dc} , V _{CE} = 5.0 V _{dc}) (I _C = 1.0 A _{dc} , V _{CE} = 5.0 V _{dc}) (I _C = 2.0 A _{dc} , V _{CE} = 5.0 V _{dc}) | h _{FE} | 70 50 10 | – – – | – |
| Collector–Emitter Saturation Voltage (I _C = 1.0 A _{dc} , I _B = 0.1 A _{dc}) | V _{CE(sat)} | – | 0.5 | V _{dc} |
| Base–Emitter On Voltage (I _C = 1.0 A _{dc} , V _{CE} = 5.0 V _{dc}) | V _{BE(on)} | – | 1.0 | V _{dc} |
| DYNAMIC CHARACTERISTICS | | | | |
| Current Gain – Bandwidth Product (Note 2) (I _C = 500 mA _{dc} , V _{CE} = 10 V _{dc} , f _{test} = 1.0 MHz) | f _T | 30 | – | MHz |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%.
2. f_T = |h_{fe}| • f_{test}.

MJE15032 (NPN), MJE15033 (PNP)

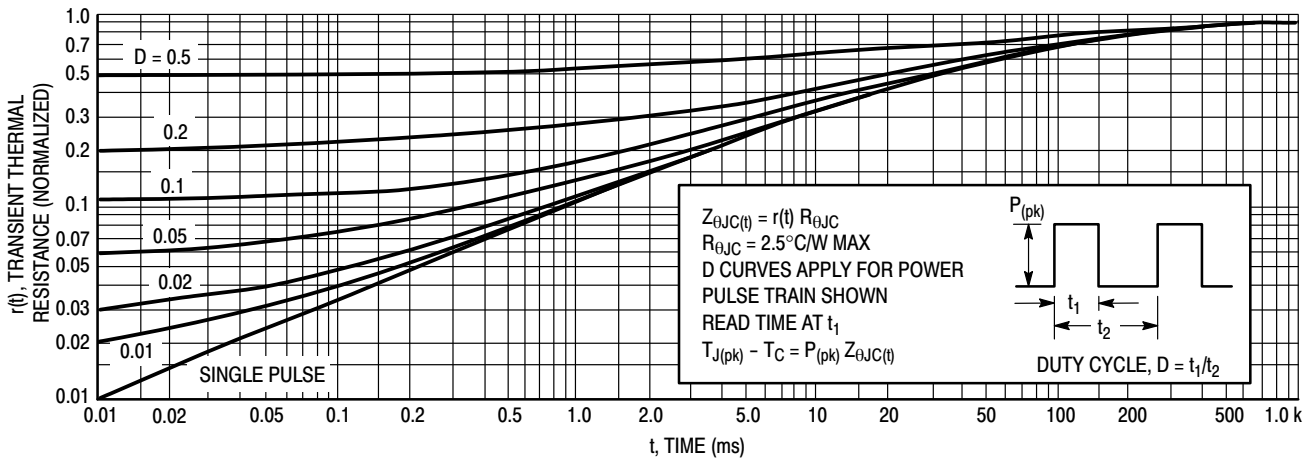


Figure 1. Thermal Response

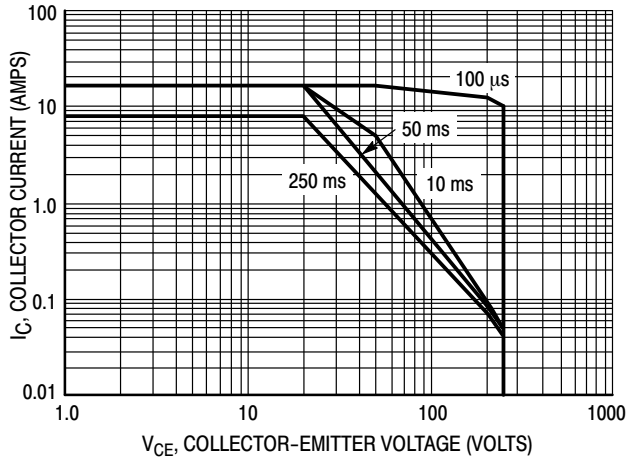


Figure 2. MJE15032 & MJE15033 Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figures 2 and 4 is based on $T_{J(pk)} = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} < 150^\circ\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 1. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

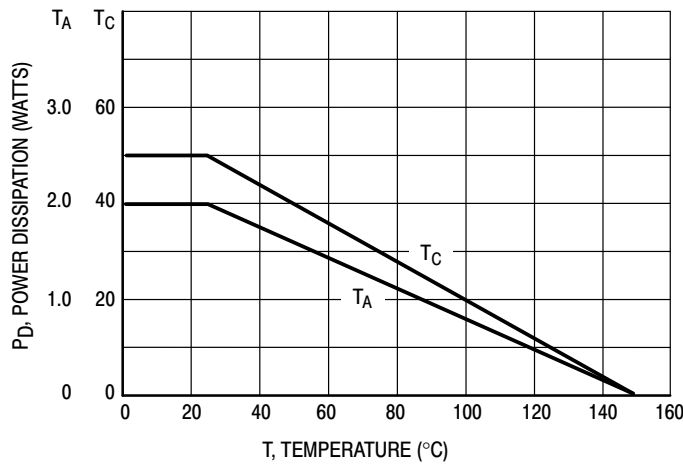


Figure 3. Power Derating

MJE15032 (NPN), MJE15033 (PNP)

NPN – MJE15032

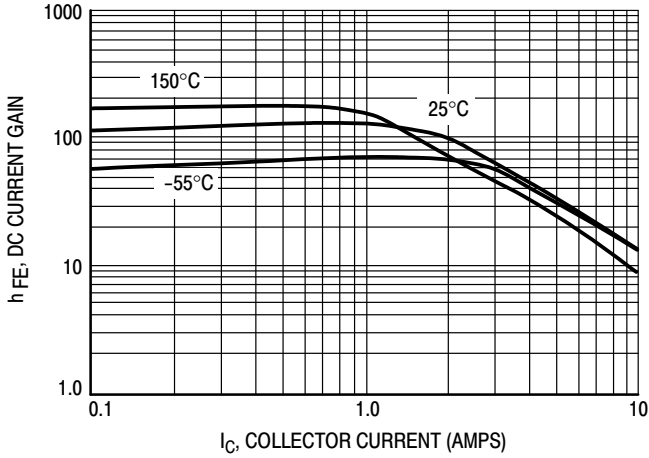


Figure 4. NPN – MJE15032
 $V_{CE} = 5$ V DC Current Gain

PNP – MJE15033

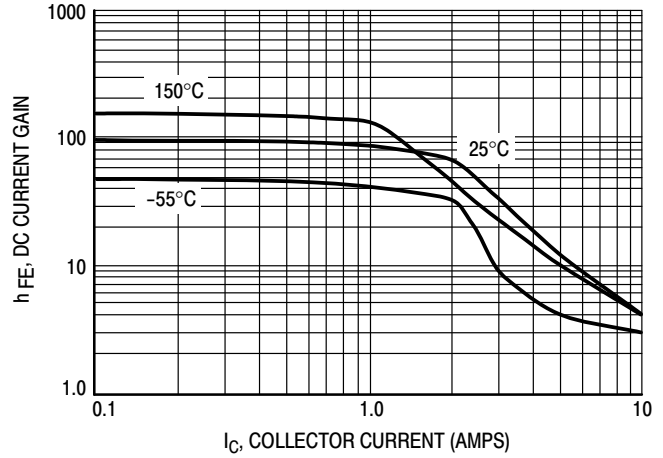


Figure 5. PNP – MJE15033
 $V_{CE} = 5$ V DC Current Gain

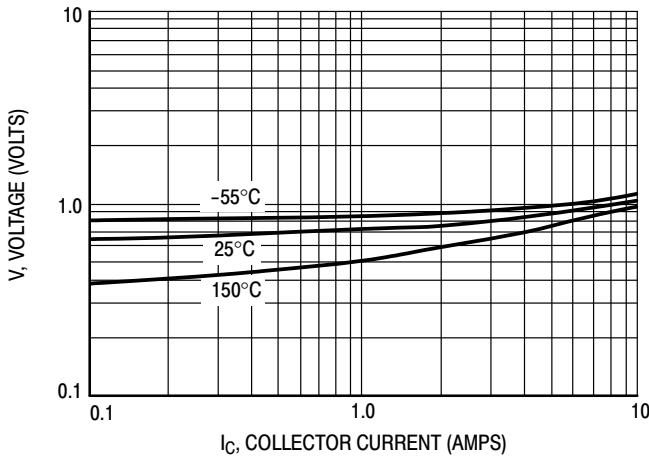


Figure 6. NPN – MJE15032
 $V_{CE} = 5$ V $V_{BE(on)}$ Curve

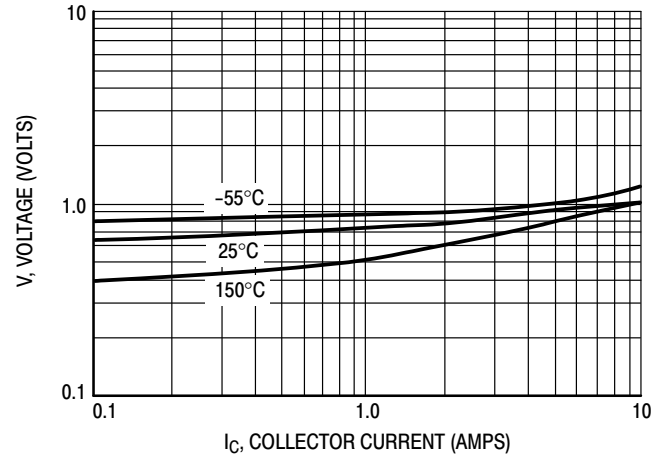


Figure 7. PNP – MJE15033
 $V_{CE} = 5$ V $V_{BE(on)}$ Curve

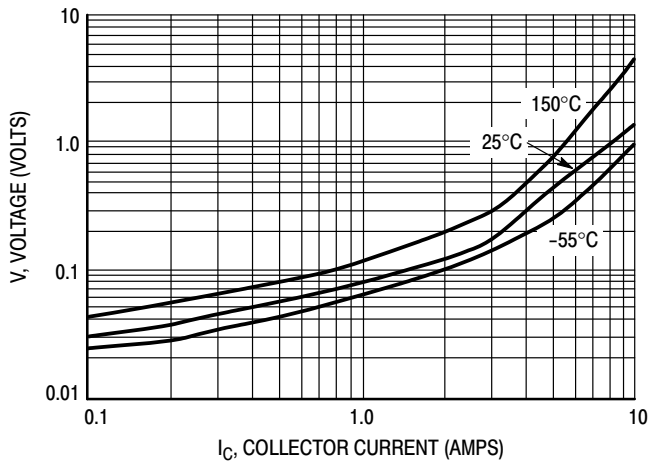


Figure 8. NPN – MJE15032
 $V_{CE(sat)}$ $I_C/I_B = 10$

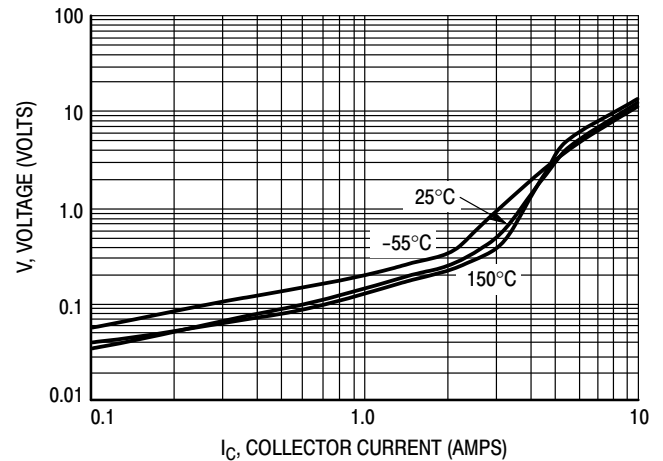


Figure 9. PNP – MJE15033
 $V_{CE(sat)}$ $I_C/I_B = 10$

MJE15032 (NPN), MJE15033 (PNP)

NPN – MJE15032

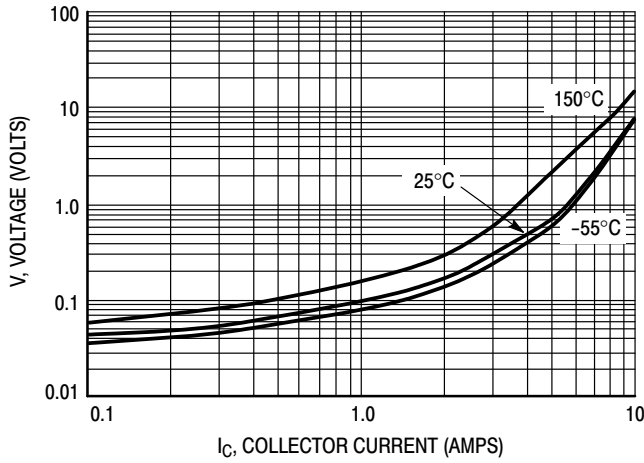


Figure 10. NPN – MJE15032
 $V_{CE(sat)} I_C/I_B = 20$

PNP – MJE15033

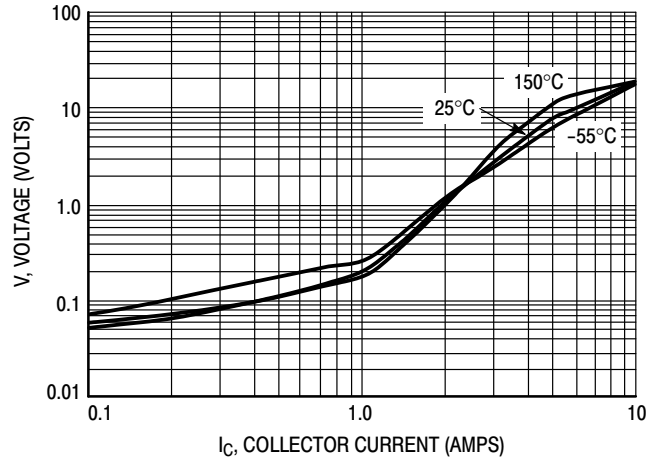


Figure 11. PNP – MJE15033
 $V_{CE(sat)} I_C/I_B = 20$

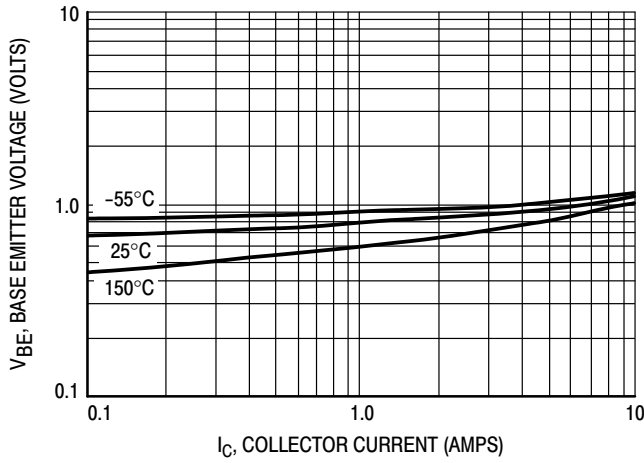


Figure 12. NPN – MJE15032
 $V_{BE(sat)} I_C/I_B = 10$

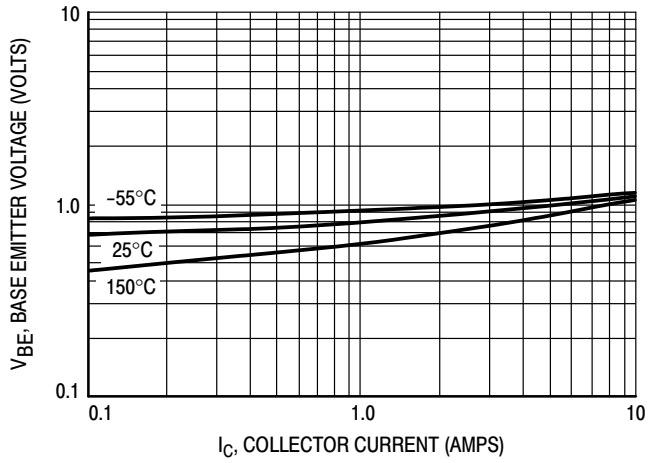
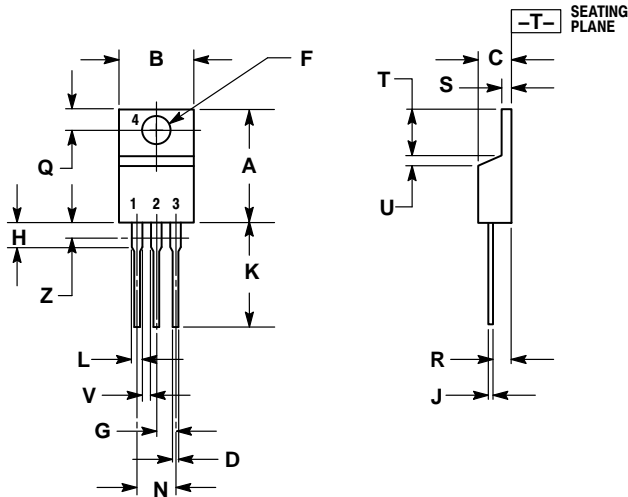


Figure 13. PNP – MJE15033
 $V_{BE(sat)} I_C/I_B = 10$

MJE15032 (NPN), MJE15033 (PNP)

PACKAGE DIMENSIONS

TO-220
CASE 221A-09
ISSUE AH



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.415 | 9.66 | 10.53 |
| C | 0.160 | 0.190 | 4.07 | 4.83 |
| D | 0.025 | 0.038 | 0.64 | 0.96 |
| F | 0.142 | 0.161 | 3.61 | 4.09 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.161 | 2.80 | 4.10 |
| J | 0.014 | 0.024 | 0.36 | 0.61 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

STYLE 1:

1. BASE
2. COLLECTOR
3. EMITTER
4. COLLECTOR

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